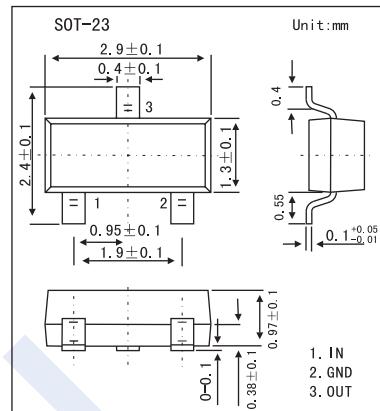
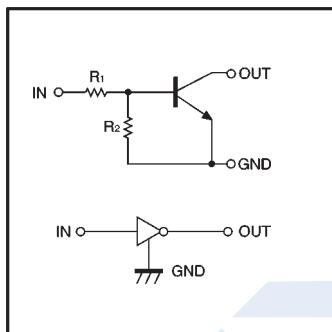


Digital Transistors

DTC114EK (KDTC114EK)

■ Features

- Repetitive peak off-state voltages :50V
- The bias resistors consist of thinfilm resistors with complete isolation to allow negative biasing of the input.
- Only the on/off conditions need to be set for operation, making device design easy.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Supply Voltage	Vcc	50	V
Input Voltage	Vin	-10~+40	V
Output Current	Io	50	mA
	IC (maxc)	100	
Power Dissipation	Pd	150	mW
Junction Temperature	Tj	150	°C
Storage temperature range	Tstg	-55 to 150	

Digital Trtansistors

DTC114EK (KDTC114EK)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Unit
Input Voltage	V _{I(off)}	V _{CC} =5V,I _O =100μA			0.5	V
	V _{I(on)}	V _O =0.3V,I _O =10mA	3			
Output Voltage	V _{O(on)}	I _O =10mA,I _I =0.5mA	3	0.1	0.3	
Input Current	I _I	V _I =5V		0.1	0.88	mA
Output Current	I _{O(off)}	V _{CC} =50V,V _I =0V			0.5	μA
DC Current Gain	G _I	V _O =5V,I _O =5mA	30			
Input Resistance	R ₁		7	10	13	kΩ
Resistance Ratio	R ₂ /R ₁		0.8	1	1.2	
Transition Frequency	f _T	V _{CE} =5V,I _E =-5mA,f=100MHz		250		MHz

■ Marking

Marking	24
---------	----

Digital Transistors

DTC114EK (KDTC114EK)

■ Typical Characteristics

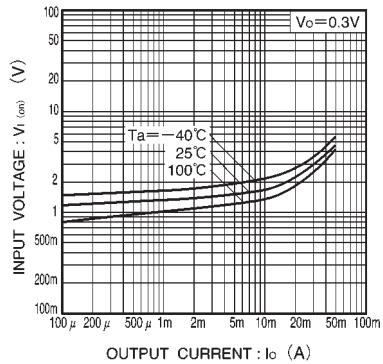


Fig.1 Input voltage vs. output current
(ON characteristics)

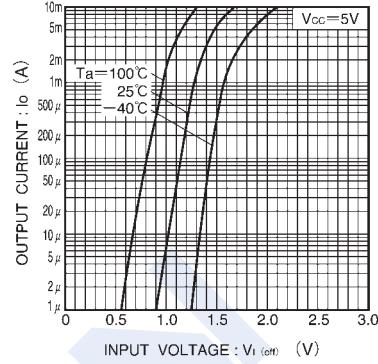


Fig.2 Output current vs. input voltage
(OFF characteristics)

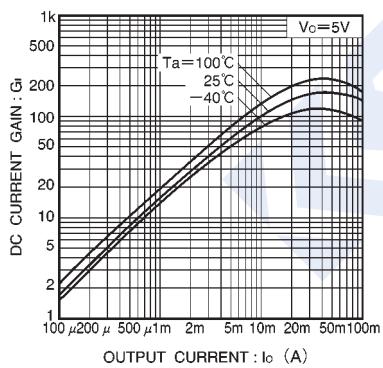


Fig.3 DC current gain vs. output current

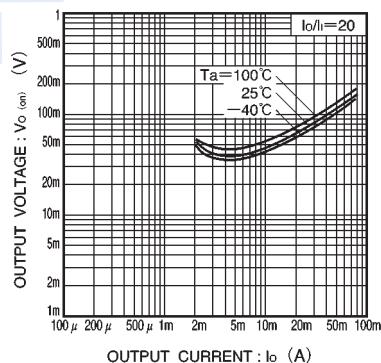


Fig.4 Output voltage vs. output current